

2 Mbit ROM + 1 Mbit / 2Mbit / 256 Kbit SRAM

ROM/RAM Combo

SST30VR021 / SST30VR022 / SST30VR023



Data Sheet

FEATURES:

- **ROM + SRAM ROM/RAM Combo**
 - SST30VR021: 256K x8 ROM + 128K x8 SRAM
 - SST30VR022: 256K x8 ROM + 256K x8 SRAM
 - SST30VR023: 256K x8 ROM + 32K x8 SRAM
- **ROM/RAM combo on a monolithic chip**
- **Equivalent ComboMemory (Flash + SRAM):**
SST31LF021E for code development and pre-production
- **Wide Operating Voltage Range: 2.7-3.3V**
- **Chip Access Time**
 - SST30VR022 70 ns
 - SST30VR021/023 500 ns
- **Low Power Dissipation:**
 - Standby: 3 μ W (Typical)
 - Operating: 10 mW (Typical)
- **Fully Static Operation**
 - No clock or refresh required
- **Three state Outputs**
- **Packages Available**
 - 32-pin TSOP (8mm x14mm)

PRODUCT DESCRIPTION

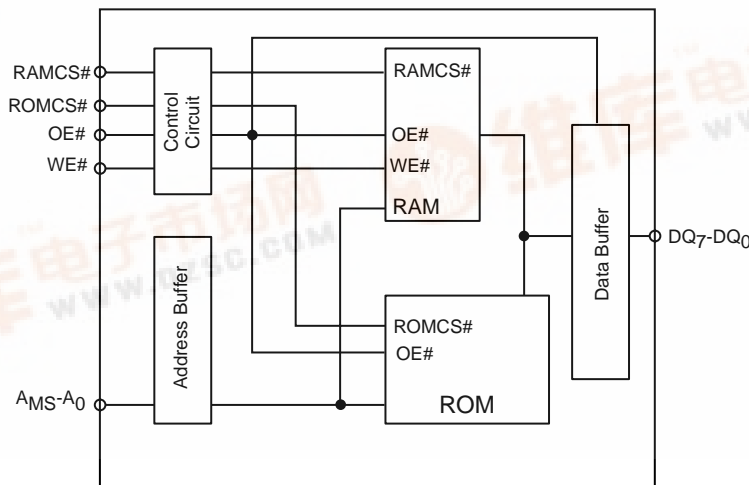
The SST30VR021/022/023 are ROM/RAM combo chips consisting of 2 Mbit Read Only Memory organized as 256 KBytes and Static Random Access Memory organized as 128, 256, and 32 KBytes.

The device is fabricated using SST's advanced CMOS low power process technology.

The SST30VR021/022/023 has an output enable input for precise control of the data outputs. It also has two (2) separate chip enable inputs for selection of either RAM or ROM and for minimizing current drain during power-down mode.

The SST30VR021/022/023 is particularly well suited for use in low voltage (2.7-3.3V) supplies such as pagers, organizers and other handheld applications.

FUNCTIONAL BLOCK DIAGRAM



Note: AMS = Most Significant Address

380 ILL B1.1





**2 Mbit ROM + 1 Mbit / 2Mbit / 256 Kbit SRAM
ROM/RAM Combo
SST30VR021 / SST30VR022 / SST30VR023**

Data Sheet

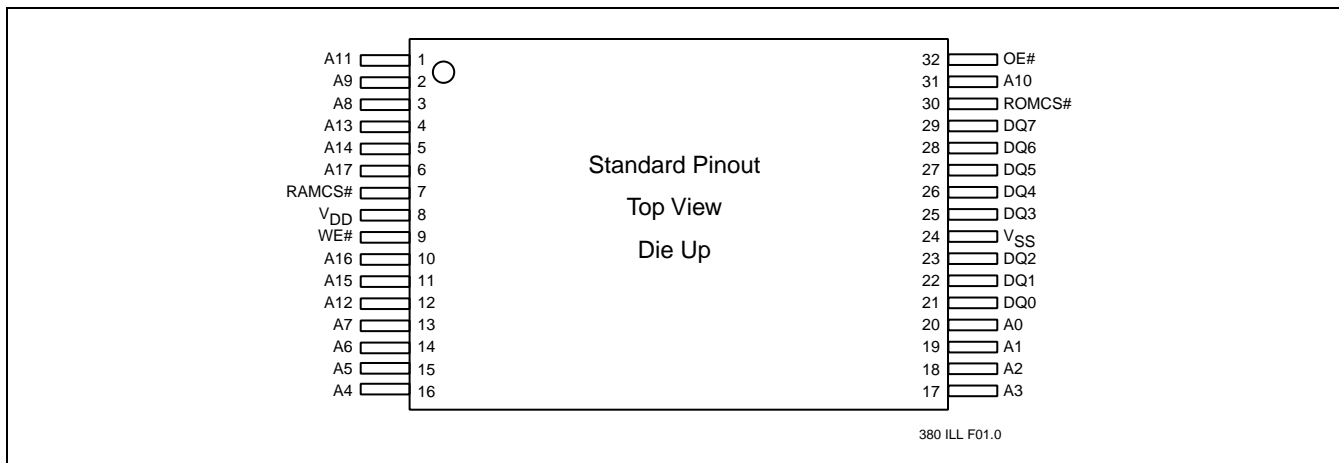


FIGURE 1: PIN ASSIGNMENTS FOR 32-PIN TSOP

TABLE 1: PIN DESCRIPTION

Symbol	Pin Name
$A_{MS}^1-A_0$	Address Inputs, for ROM: $A_{MS} = A_{17}$, for RAM: $A_{MS} = A_{16}$ for SST30VR021 A_{17} for SST30VR022 A_{14} for SST30VR023
WE#	Write Enable Input
OE#	Output Enable
RAMCS#	RAM Enable Input
ROMCS#	ROM Enable Input
DQ ₇ -DQ ₀	Data Input/Output
V _{DD}	Power Supply
V _{SS}	Ground

1. A_{MS} = Most significant address

**2 Mbit ROM + 1 Mbit / 2Mbit / 256 Kbit SRAM
ROM/RAM Combo
SST30VR021 / SST30VR022 / SST30VR023**



Data Sheet

Absolute Maximum Stress Ratings (Applied conditions greater than those listed under “Absolute Maximum Stress Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this data sheet is not implied. Exposure to absolute maximum stress rating conditions may affect device reliability.)

Operating Temperature -20°C to +85°C
 Storage Temperature -65°C to +150°C
 Voltage on Any Pin Relative to V_{SS} -0.5V to V_{DD} + 0.5V
 Voltage on V_{DD} Supply Relative to V_{SS} -0.5V to 4.0V
 Power Dissipation..... 1.0W
 Soldering Temperature (10 Seconds Lead Only) 260°C

OPERATING RANGE

Range	Ambient Temp	V _{DD}
Commercial	0°C to +70°C	2.7-3.3V
Extended	-20°C to +85°C	2.7-3.3V

AC CONDITIONS OF TEST

Input Pulse Level.....	0-V _{DD}
Input & Output Timing Reference Levels.....	V _{DD} /2
Input Rise/Fall Time.....	5 ns
Output Load.....	C _L = 30 pF for 70 ns
Output Load.....	C _L = 100 pF for 500 ns

TABLE 2: RECOMMENDED DC OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Units
V _{DD}	Supply Voltage	2.7	3.3	V
V _{SS}	Ground	0	0	V
V _{IH}	Input High Voltage	2.4	V _{DD} + 0.5	V
V _{IL}	Input Low Voltage	-0.3	0.3	V

T2.0 380

TABLE 3: DC OPERATING CHARACTERISTICS

Symbol	Parameter	V _{DD} = 3.0 ± 0.3V			Test Conditions
		Min	Max	Units	
I _{DD1}	ROM Operating Supply Current		4.0+1.1(f) ¹	mA	ROMCS#=V _{IL} , RAMCS#=V _{IH} , V _{IN} =V _{IH} or V _{IL} , I _{I/O} =Opens
I _{DD2}	RAM Operating Supply Current		2.5+1(f) ¹	mA	ROMCS#=V _{IH} , RAMCS#=V _{IL} , I _{I/O} =Opens
I _{SB}	Standby V _{DD} Current		10	µA	ROMCS#≥V _{DD} -0.2V, RAMCS#≥V _{DD} -0.2V V _{IN} ≥V _{DD} -0.2V or V _{IN} ≤0.2V
I _{LI}	Input Leakage Current	-1	1	µA	V _{IN} =V _{SS} to V _{DD}
I _{LO}	Output Leakage Current	-1	1	µA	ROMCS#=RAMCS#=V _{IH} or OE#=V _{IH} or WE#=V _{IL} , V _{I/O} =V _{SS} to V _{DD}
V _{OL}	Output Low Voltage		0.4	V	I _{OL} = 1.0 mA
V _{OH}	Output High Voltage	2.2		V	I _{OH} = -0.5 mA

T3.3 380

1. f = Frequency of operation (MHz) = 1/cycle time



**2 Mbit ROM + 1 Mbit / 2Mbit / 256 Kbit SRAM
ROM/RAM Combo
SST30VR021 / SST30VR022 / SST30VR023**

Data Sheet

TABLE 4: CAPACITANCE ($T_a = 25^\circ\text{C}$, $f=1\text{ Mhz}$)

Parameter	Description	Test Condition	Maximum
$C_{I/O}^1$	I/O Pin Capacitance	$V_{I/O} = 0V$	8 pF
C_{IN}^1	Input Capacitance	$V_{IN} = 0V$	6 pF

T4.1 380

1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

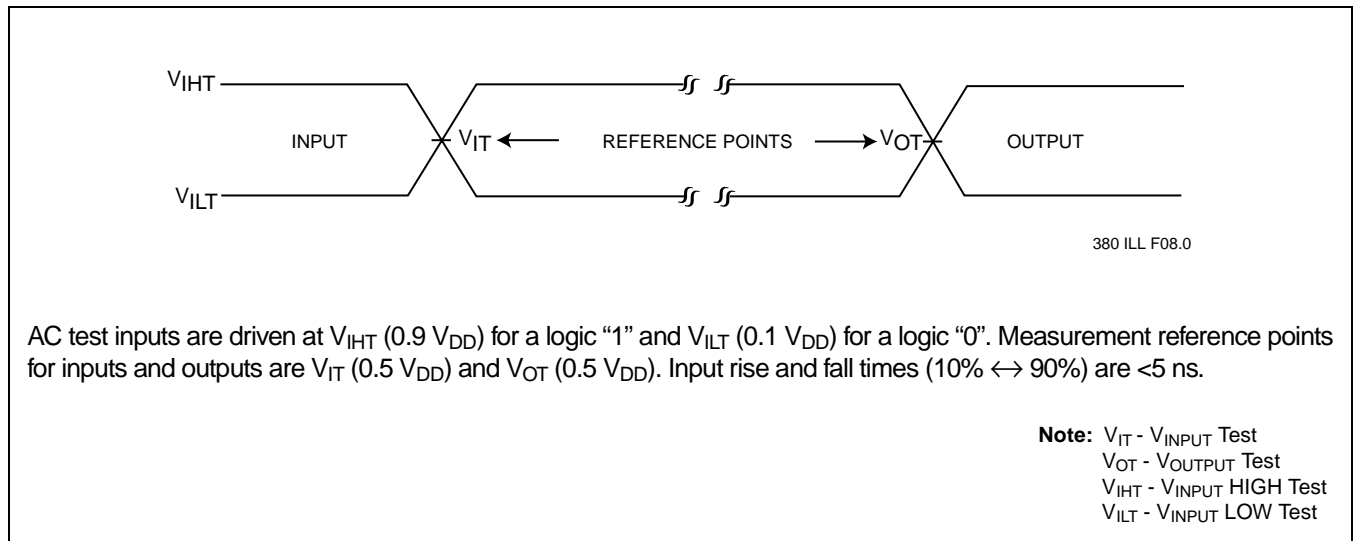


FIGURE 2: AC INPUT/OUTPUT REFERENCE WAVEFORMS

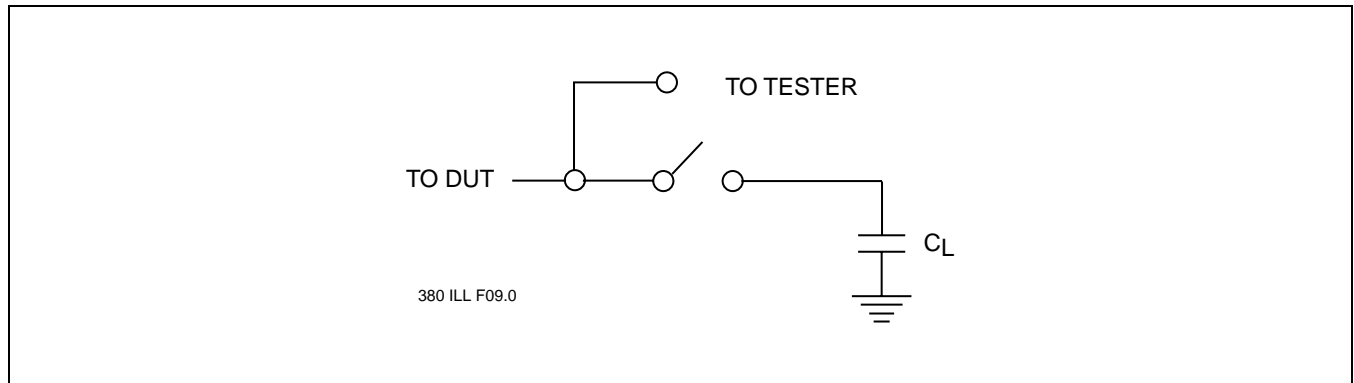


FIGURE 3: A TEST LOAD EXAMPLE

**2 Mbit ROM + 1 Mbit / 2Mbit / 256 Kbit SRAM
ROM/RAM Combo
SST30VR021 / SST30VR022 / SST30VR023**



Data Sheet

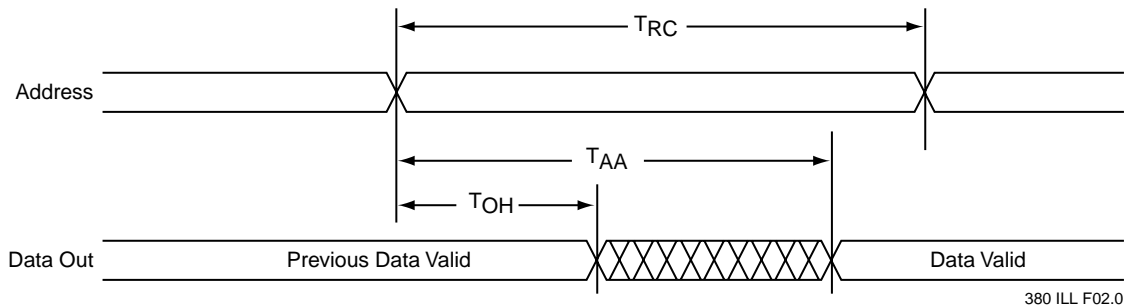
AC CHARACTERISTICS

I. ROM Operation

TABLE 5: READ CYCLE TIMING PARAMETERS $V_{DD} = 3.0V \pm 0.3$

Symbol	Parameter	SST30VR022-70		SST30VR021/023-500		Units
		Min	Max	Min	Max	
T_{RC}	Read Cycle Time	70		500		ns
T_{AA}	Address Access Time		70		500	ns
T_{CO}	Chip Select to Output		70		500	ns
T_{OE}	Output Enable to Valid Output		35		250	ns
T_{LZ}	Chip Select to Low-Z Output	0		25		ns
T_{OLZ}	Output Enable to Low-Z Output	0		25		ns
T_{HZ}	Chip Disable to High-Z Output		25		30	ns
T_{OHZ}	Output Disable to High-Z Output		25		30	ns
T_{OH}	Output Hold from Address Change	10		15		ns

T5.1 380



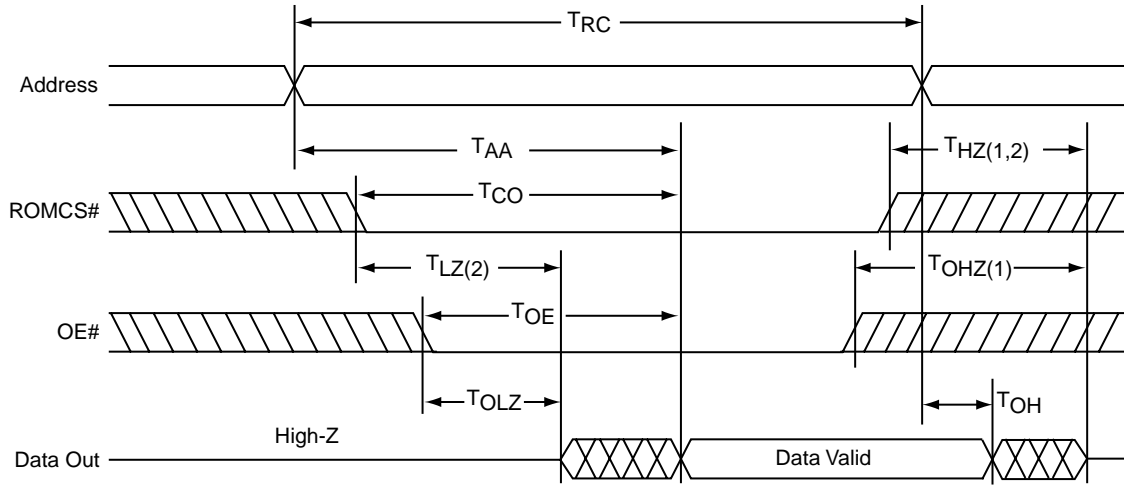
380 ILL F02.0

FIGURE 4: ROM READ CYCLE TIMING DIAGRAM (ADDRESS CONTROLLED) (ROMCS# = OE# = V_{IL})



2 Mbit ROM + 1 Mbit / 2Mbit / 256 Kbit SRAM
ROM/RAM Combo
SST30VR021 / SST30VR022 / SST30VR023

Data Sheet



380 ILL F03.0

- Notes:
1. T_{HZ} and T_{OHZ} are defined as the time at which the outputs achieve the open circuit condition and are referenced to the V_{OH} or V_{OL} .
 2. At any given temperature and voltage condition $T_{HZ}(\max)$ is less than $T_{LZ}(\min)$ both for a given device and from device to device.

FIGURE 5: ROM READ CYCLE TIMING DIAGRAM (ROMCS# & OE# CONTROLLED)

**2 Mbit ROM + 1 Mbit / 2Mbit / 256 Kbit SRAM
ROM/RAM Combo
SST30VR021 / SST30VR022 / SST30VR023**



Data Sheet

II. SRAM Operation (ROMCS# = V_{IH})

TABLE 6: READ CYCLE TIMING PARAMETERS V_{DD} = 3.0V±0.3

Symbol	Parameter	SST30VR022-70		SST30VR021/023-500		Units
		Min	Max	Min	Max	
T _{RC}	Read Cycle Time	70		500		ns
T _{AA}	Address Access Time		70		500	ns
T _{CO}	Chip Select to Output		70		500	ns
T _{OE}	Output Enable to Valid Output		35		250	ns
T _{LZ}	Chip Select to Low-Z Output	0		25		ns
T _{HZ}	Chip Disable to High-Z Output		25		30	ns
T _{OZH}	Output Disable to High-Z Output		25		30	ns
T _{OH}	Output Hold from Address Change	10		15		ns

T6.2 380

TABLE 7: WRITE CYCLE TIMING PARAMETERS V_{DD} = 3.0V±0.3

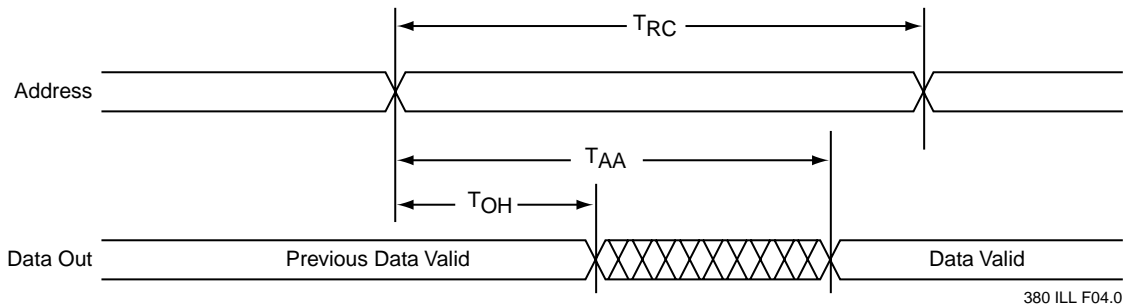
Symbol	Parameter	SST30VR022-70		SST30VR021/023-500		Units
		Min	Max	Min	Max	
T _{WC}	Write Cycle Time	70		500		ns
T _{CW}	Chip Select to End-of-Write	60		365		ns
T _{AW}	Address Valid to End-of-Write	60		375		ns
T _{AS}	Address Set-up Time	0		0		ns
T _{WP}	Write Pulse Width	60		375		ns
T _{WR}	Write Recovery Time	0		0		ns
T _{WHZ}	Write to Output High-Z		30		80	ns
T _{DW}	Data to Write Time Overlap	30		200		ns
T _{DH}	Data Hold from Write Time	0		0		ns
T _{OW}	End Write to Output Low-Z	0		15		ns

T7.1 380



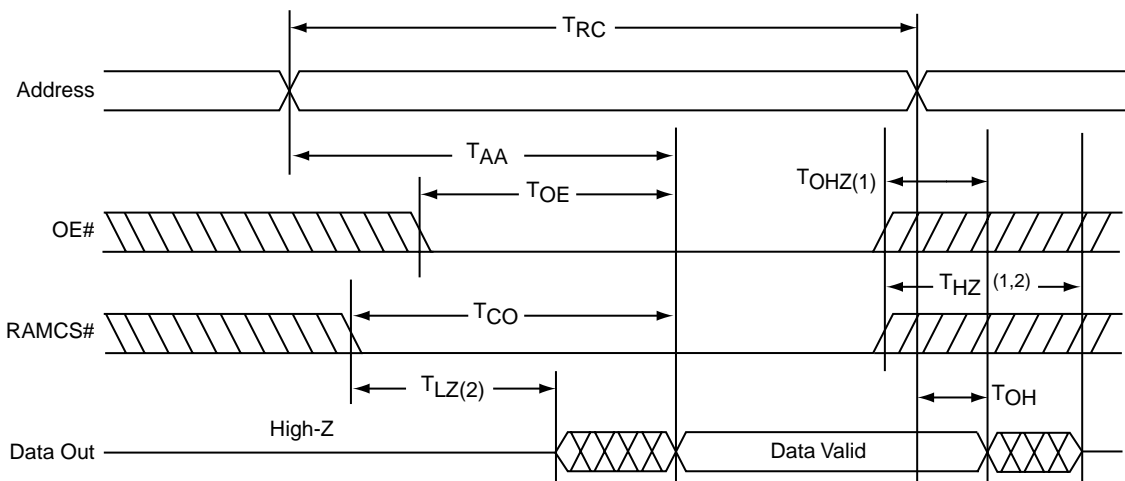
2 Mbit ROM + 1 Mbit / 2Mbit / 256 Kbit SRAM
 ROM/RAM Combo
 SST30VR021 / SST30VR022 / SST30VR023

Data Sheet



380 ILL F04.0

FIGURE 6: SRAM READ CYCLE TIMING DIAGRAM (ADDRESS CONTROLLED) (OE# = RAMCS# = V_{IL}, WE# = V_{IH})



380 ILL F05.0

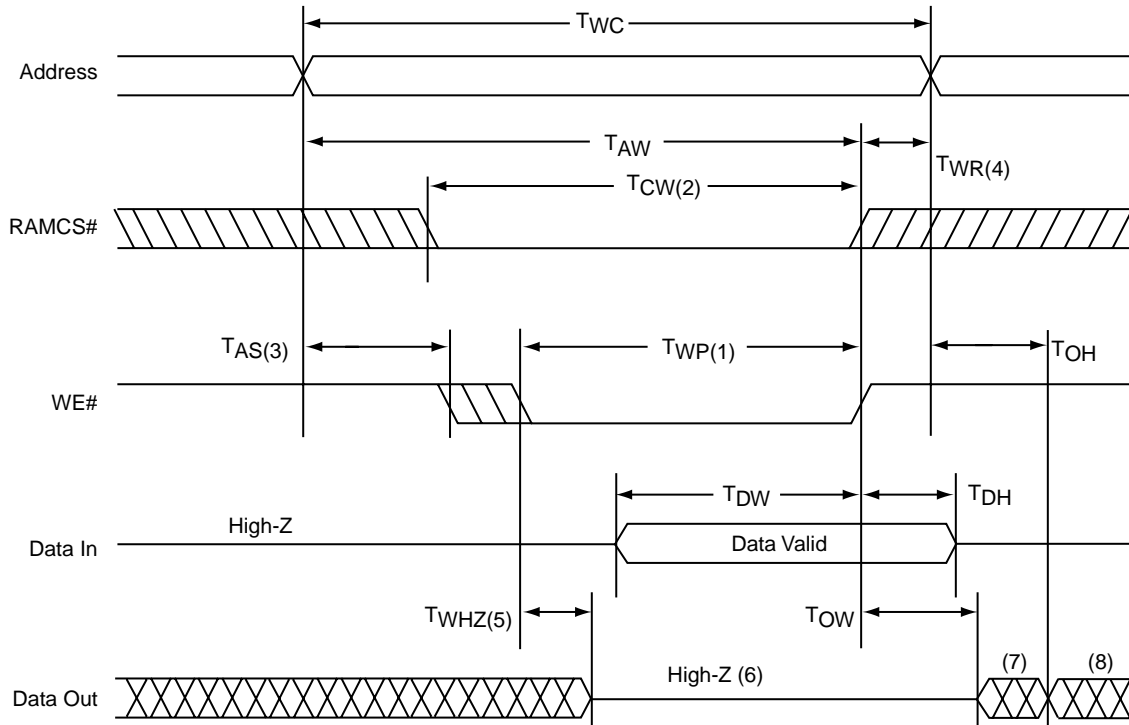
- Notes:
1. THZ and TOHZ are defined as the time at which the outputs achieve the open circuit condition and are referenced to the VOH or VOL.
 2. At any given temperature and voltage condition THZ(max) is less than TLZ(min) both for a given device and from device to device.
 3. WE# is high for Read cycle.
 4. Address valid prior to coincidence with RAMCS# transition low.

FIGURE 7: SRAM READ CYCLE TIMING DIAGRAM (OE# OR RAMCS# CONTROLLED)

2 Mbit ROM + 1 Mbit / 2Mbit / 256 Kbit SRAM
ROM/RAM Combo
SST30VR021 / SST30VR022 / SST30VR023



Data Sheet



380 ILL F07.0

- Notes:
1. A write occurs during the overlap (T_{WP}) of a low RAMCS# and low WE#. A write begins at the latest transition among RAMCS# going low and WE# going low: A write end at the earliest transition among RAMCS# going high and WE# going high, T_{WP} is measured from the beginning of write to the end of write.
 2. T_{CW} is measured from the later of RAMCS# going low to the end of write.
 3. T_{AS} is measured from the address valid to the beginning of write.
 4. T_{WR} is measured from the end of write to the address change.
 5. If RAMCS#, WE# are in the read mode during this period, the I/O pins are in the outputs Low-Z state. Inputs of opposite phase of the output must not be applied because bus contention can occur.
 6. If RAMCS# goes low simultaneously with WE# going low or after WE# going low, the outputs remain high impedance state.
 7. DO_{UT} is the same phase of the latest written data in this write cycle.
 8. DO_{UT} is the read data of new address
 9. ROMCS# = V_{IH}

FIGURE 8: SRAM WRITE CYCLE TIMING DIAGRAM

TABLE 8: FUNCTIONAL DESCRIPTION/TRUTH TABLE

Address Inputs	ROMCS# ¹	RAMCS# ¹	WE#	OE#	DQ ₀ -DQ ₇	
X	H	H	X ²	X ²	Z	Standby
A ₁₇ -A ₀	L	H	X ²	H	Z	Output Floating
A ₁₇ -A ₀	L	H	X ²	L	Dout	ROM Read
Only A _{MS} ³ -A ₀ are valid ⁴	H	L	H	H	Z	Output Floating
Only A _{MS} ³ -A ₀ are valid ⁴	H	L	H	L	Dout	RAM Read
Only A _{MS} ³ -A ₀ are valid ⁴	H	L	L	H	Din	RAM Write

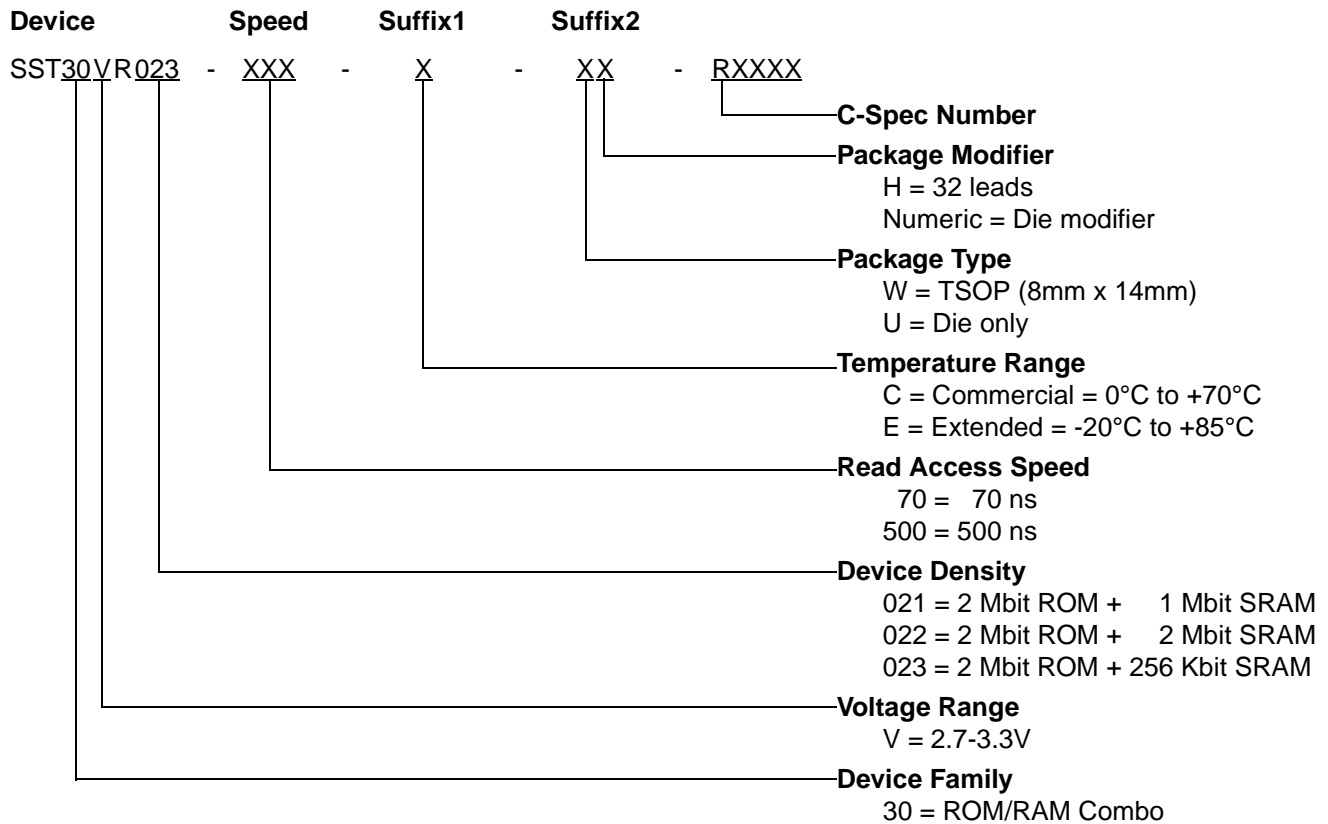
T8.4 380

1. It is forbidden for ROMCS# pin and RAMCS# pin to be "0" at the same time
2. X means Don't Care.
3. A_{MS} = A₁₆ for SST30VR021, A₁₇ for SST30VR022, and A₁₄ for SST30VR023
4. For SST30VR021: A₁₇ must be fixed to "L" or "H"
 For SST30VR023: A₁₅, A₁₆, and A₁₇ must be fixed to "L" or "H"



**2 Mbit ROM + 1 Mbit / 2Mbit / 256 Kbit SRAM
ROM/RAM Combo
SST30VR021 / SST30VR022 / SST30VR023**

Data Sheet



SST30VR021 Valid combinations

SST30VR021-500-C-WH
SST30VR021-500-C-U1
SST30VR021-500-E-WH

SST30VR022 Valid combinations

SST30VR022-70-C-WH
SST30VR022-70-C-U1
SST30VR022-70-E-WH

SST30VR023 Valid combinations

SST30VR023-500-C-WH
SST30VR023-500-C-U1
SST30VR023-500-E-WH

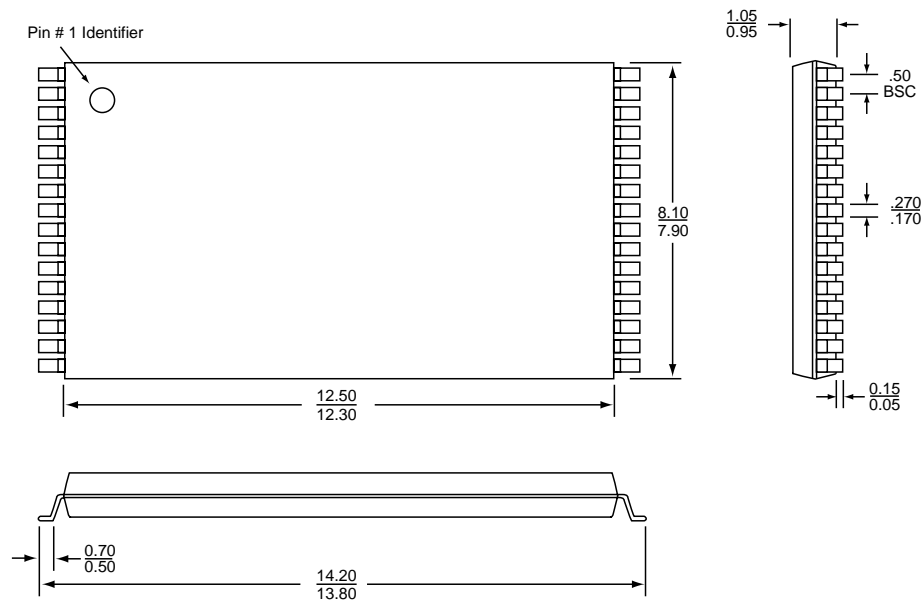
Example: Valid combinations are those products in mass production or will be in mass production. Consult your SST sales representative to confirm availability of valid combinations and to determine availability of new combinations.

**2 Mbit ROM + 1 Mbit / 2Mbit / 256 Kbit SRAM
ROM/RAM Combo
SST30VR021 / SST30VR022 / SST30VR023**



Data Sheet

PACKAGING DIAGRAMS



32.TSOP-WH-ILL.4

- Note:
1. Complies with JEDEC publication 95 MO-142 BA dimensions, although some dimensions may be more stringent.
 2. All linear dimensions are in millimeters (min/max).
 3. Coplanarity: 0.1 (± 0.05) mm.
 4. Maximum allowable mold flash is 0.15mm at the package ends, and 0.25mm between leads.

**32-PIN THIN SMALL OUTLINE PACKAGE (TSOP) 8MM X 14MM
SST PACKAGE CODE: WH**



**2 Mbit ROM + 1 Mbit / 2Mbit / 256 Kbit SRAM
ROM/RAM Combo
SST30VR021 / SST30VR022 / SST30VR023**

Data Sheet